

THANTHAI PERIYAR GOVT. INSTITUTE  
OF TECHNOLOGY, VELLORE  
DEPARTMENT OF ECE



**AN ENERGY-EFFICIENT HYBRID SRAM BASED**  
**IN-MEMORY COMPUTING ARCHITECTURE WITH INDEPENDENT**  
**GATE FINFETS**

**PROJECT GUIDE:**

Mrs. M.JANANI, M.E., Assistant Professor ECE

**TEAM MEMBERS:**

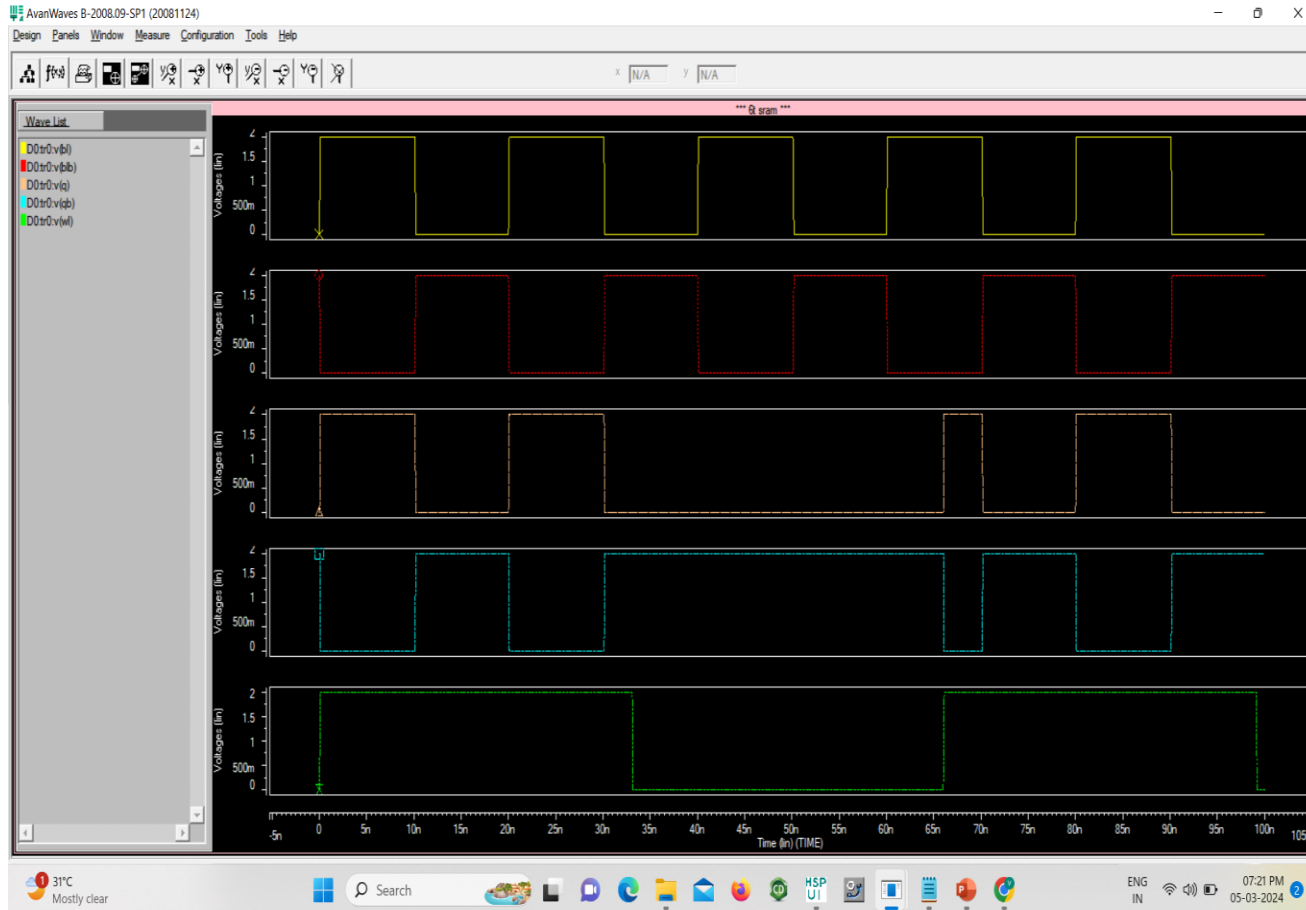
- 1) VINITHA K (513120106095)
- 2) PAVITHRA B (513120106063)
- 3) SHRUTHI B K (513120106078)

# **PROBLEM STATEMENT AND TECHNOLOGY PROPOSED**

- The Hybrid SRAM/RRAM In-Memory Computing Architecture revolves around enhancing Energy efficiency and computational performance in memory centric tasks. The challenge lies in optimizing the integration of SRAM and RRAM technologies to enhance overall performance.
- The goal is to develop a flexible and efficient solution to implement all Boolean functions and also to overcome memory wall.
- Therefore, one of the most promising approaches for alleviating these challenges, **In-Memory Computing (IMC)** is proposed.
- **SOFTWARE TOOL**: SYNOPSIS HSPICE

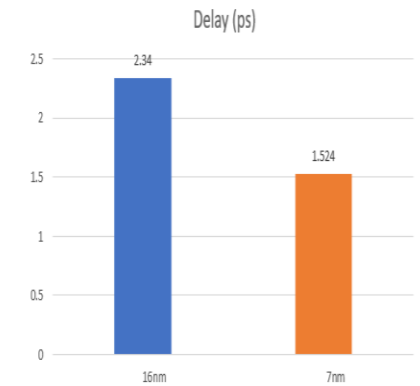
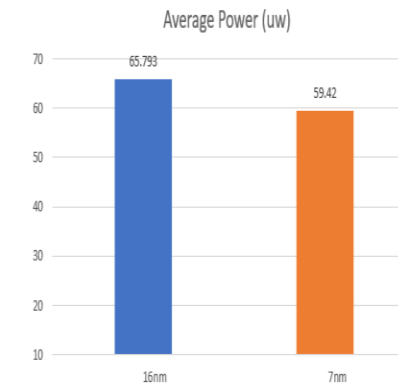
**\*\*\*Results upto First Review\*\*\***

## Implementation of 6T SRAM:

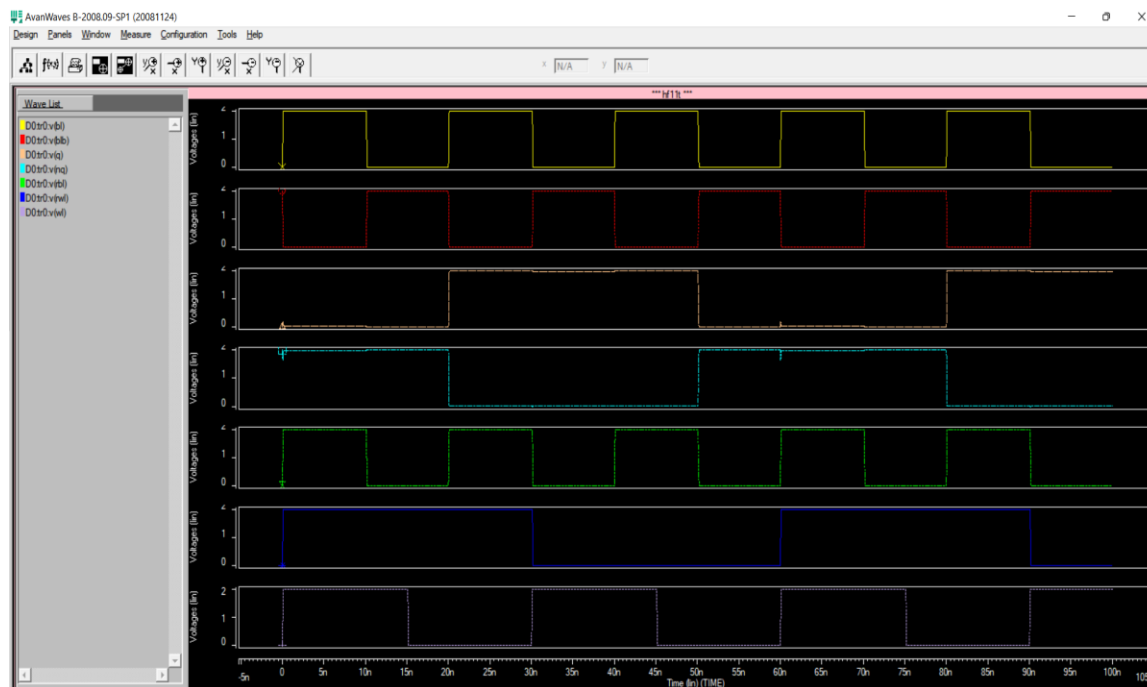
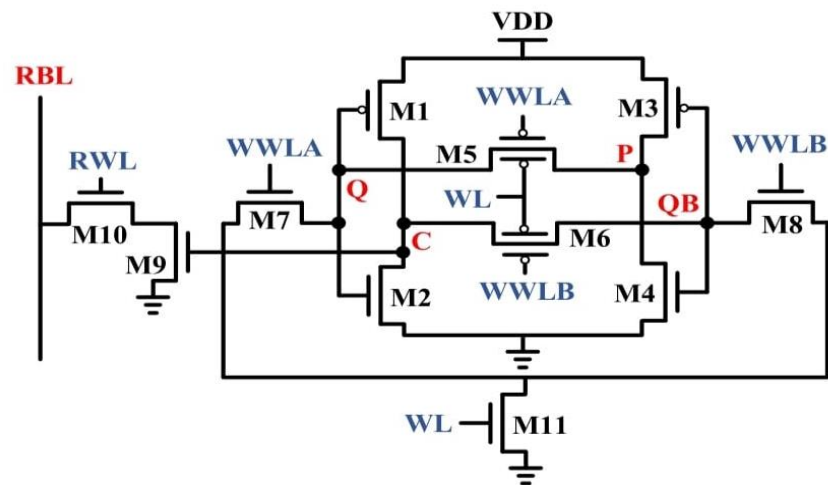


## PERFORMANCE ANALYSIS:

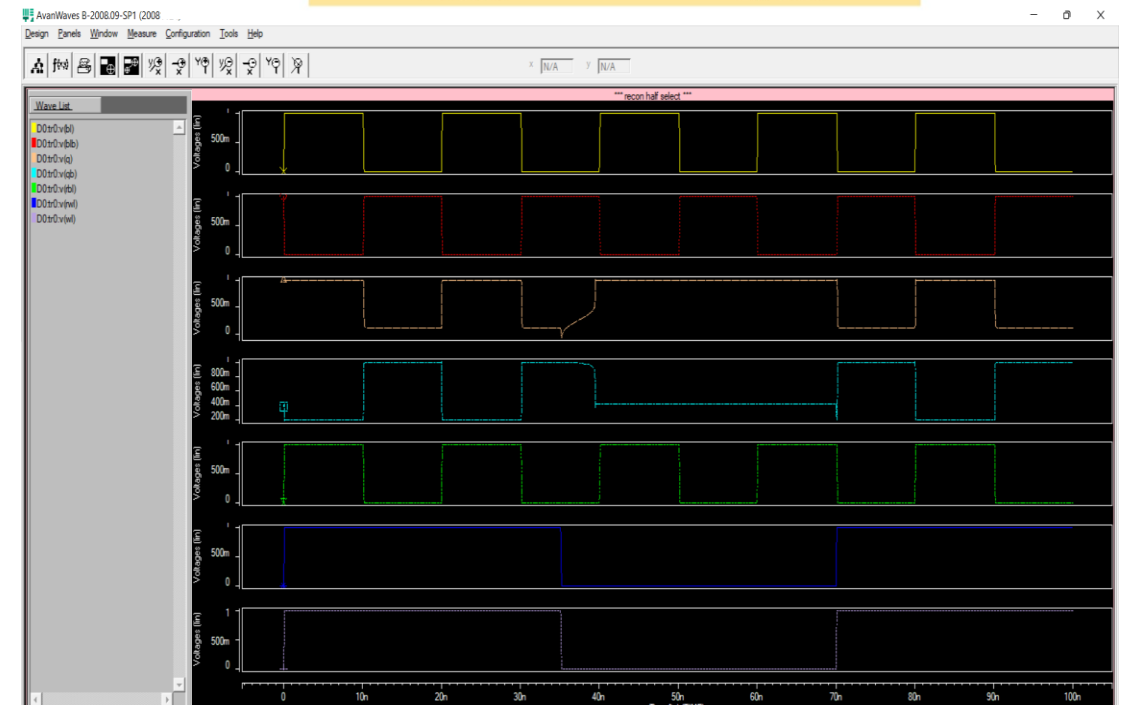
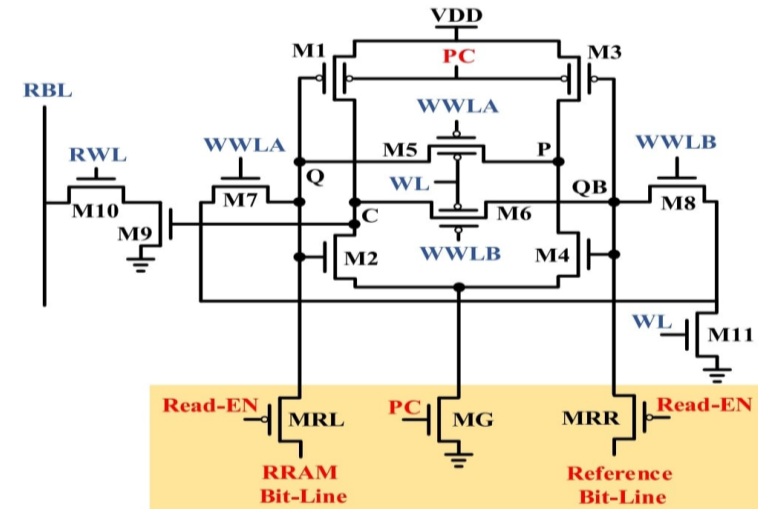
FINFET Technology	Average Power (uw)	Delay (ps)	Temperature (°C)
16nm	65.793	2.340	25
7nm	59.42	1.524	25



### Half select 1T1R1C Cell:

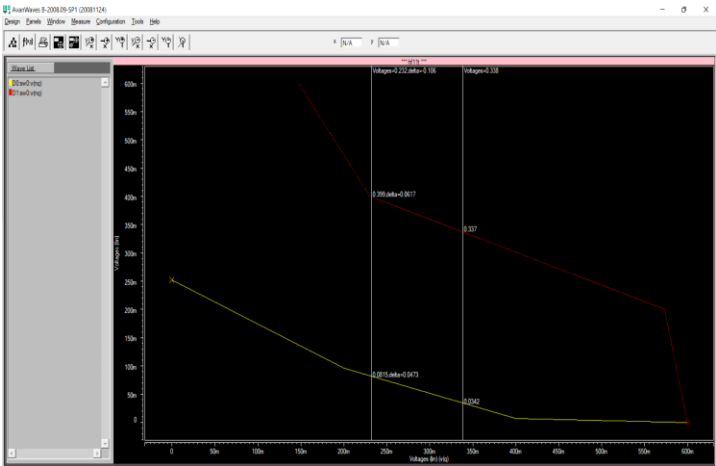
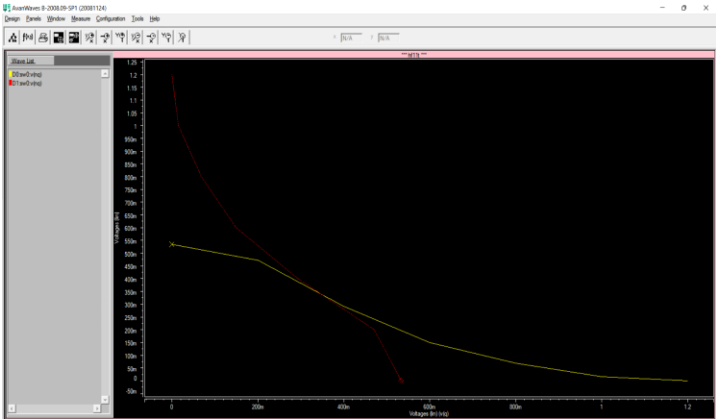
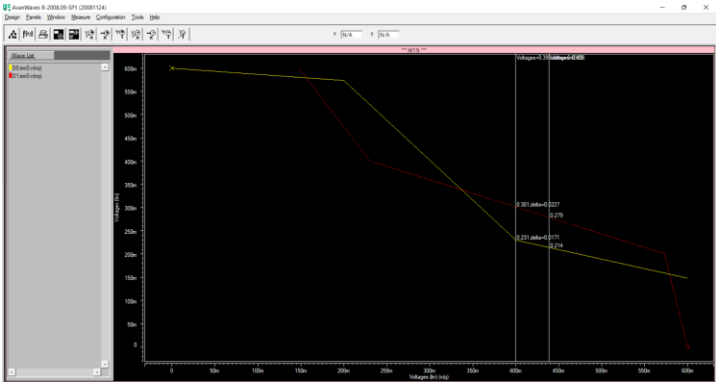


### Reconfigurable Half select 11T (HF11T):

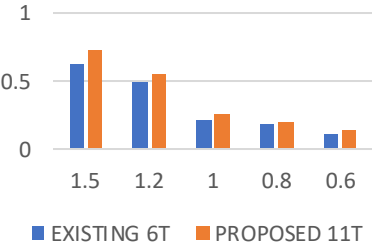


# SNM Comparison of 6T and 11T SRAM for various supply voltage:

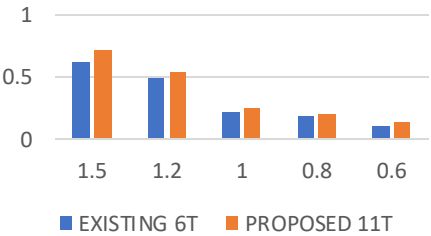
VOLTAGE(V)	RSNM(V)		HSNM(V)		WSNM(V)	
	6T SRAM	11T SRAM	6T SRAM	11T SRAM	6T SRAM	11T SRAM
1.5	0.5245	0.6169	0.0915	0.2169	0.6245	0.7224
1.2	0.4981	0.5361	0.0825	0.1123	0.4981	0.5451
1	0.2173	0.2214	0.0691	0.0742	0.2173	0.2518
0.8	0.1935	0.2048	0.0342	0.0518	0.1854	0.2948
0.6	0.1088	0.1263	0.0226	0.0299	0.1088	0.1381



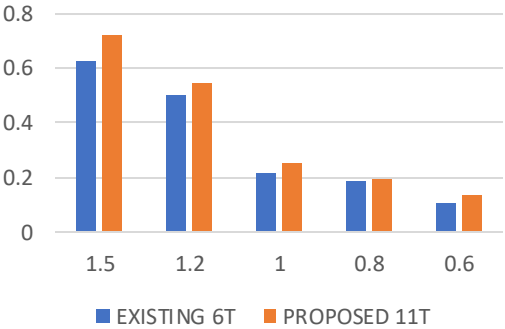
Read static noise margin



Hold static noise margin



Write static noise margin



## \*\*\*Results upto Second Review\*\*\*

### Power Comparison on Various SRAM Cells:

Power supply(v)	Read static power(mw)		Hold static power(mw)		Write static power(mw)	
	6T SRAM	11T SRAM	6T SRAM	11T SRAM	6T SRAM	11T SRAM
1.2	1.734	0.568	1.321	0.780	0.4525	0.350
2	2.059	1.2248	2.7978	2.4306	1.9262	1.4549

### Design of logic mode in polymorphic unit [PMU]:

